ELECTRONICS, INC.
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2N2925
Silicon NPN Transistor
General Purpose
TO–92 Type Package

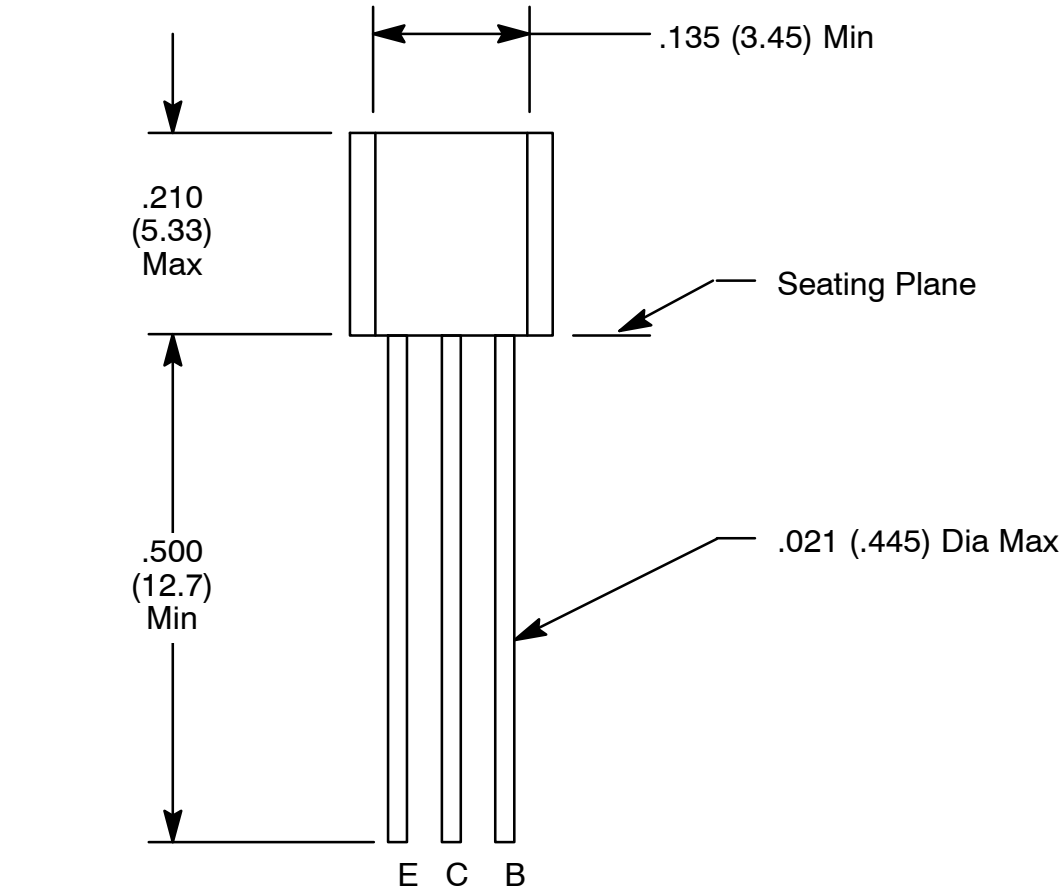
Absolute Maximum Ratings:

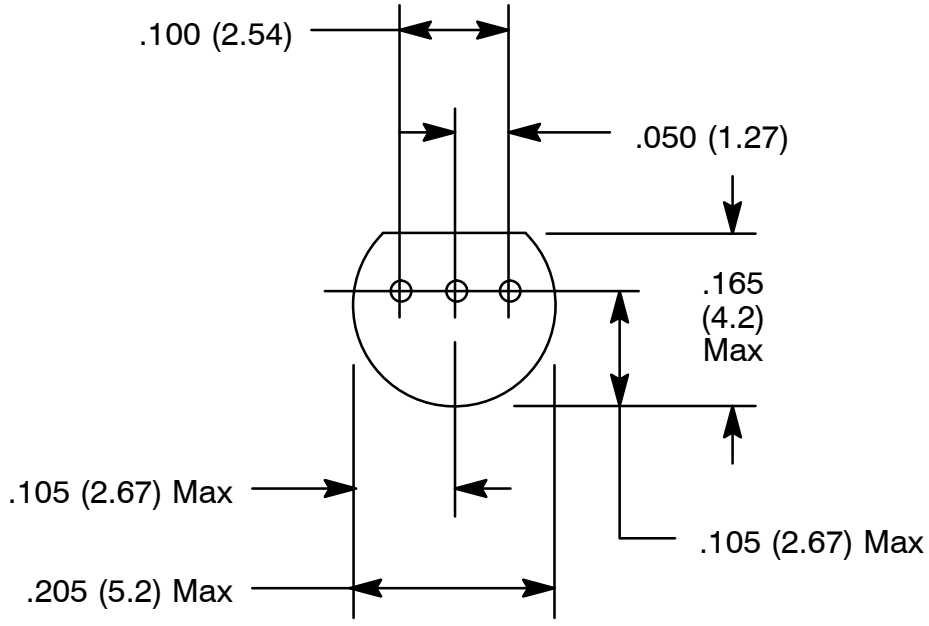
Collector–Emitter Voltage, V_{CEO} 25V
Collector–Base Voltage, V_{CBO} 25V
Emitter–Base Voltage, V_{EBO} 5V
Continuous Collector Current (Note 1), I_C 100mA
Total Power Dissipation ($T_A \le +25°C$), P_T 360mW
Derate Above +25°C . . . . . 3.6mW/°C
Total Power Dissipation ($T_A \le +55°C$), P_T 250mW
Derate Above +25°C . . . . . 3.6mW/°C
Operating Junction Temperature Range, T_J . . . . . –55° to +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C
Lead Temperature (During Soldering, 1/16” from case, 10sec max), T_L . . . . . +260°C

Note 1. Determined from power limitations due to saturation voltages at this current

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 25V	–	–	0.1	μA
		V_{CB} = 25V, T_A = +100°C	–	–	15	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 5V	–	–	0.1	μA
DC Forward Current Transfer Ratio	h_{FE}	V_{CE} = 4.5V, I_C = 2mA	–	215	–	
Small–Signal Forward Current Transfer Ratio	h_{fe}	V_{CE} = 10V, I_C = 2mA, f = 1kHz	235	–	–	
Input Impedance	h_{fb}	V_{CE} = 10V, I_C = 2mA, f = 1kHz	–	15	–	Ω
Gain Bandwidth Product	f_T	V_{CB} = 5V, I_C = 4mA	–	160	–	MHz
Noise Figure	NF	I_C = 100μA, V_{CE} = 5V, R_g = 2000Ω, f = 10kHz, BW = 1Hz	–	2.6	–	dB
Collector Capacitance	C_{cbo}	V_{CB} = 10V, I_E = 0, f = 1MHz	4.5	7.0	10	pF


.135 (3.45) Min
.210
(5.33)
Max
Seating Plane
.500
(12.7)
Min
.021 (.445) Dia Max
E C B


.100 (2.54)
.050 (1.27)
.165
(4.2)
Max
.105 (2.67) Max
.105 (2.67) Max
.205 (5.2) Max